

INA250-Q1 集成有精密分流电阻的汽车类 36V 低侧或高侧双向零漂移分流监视器

1 特性

- 适用于汽车电子 应用
- 具有符合 AEC-Q100 标准的下列结果：
 - 器件温度 1 级：-40°C 至 +125°C 的环境运行温度范围
 - 器件人体模型 (HBM) 静电放电 (ESD) 分类等级 2
 - 器件组件充电模式 (CDM) ESD 分类等级 C5
- 集成有精密分流电阻：
 - 分流电阻：2mΩ
 - 分流电阻容差：0.1% (最大值)
 - 15A 持续电流 (-40°C 至 +85°C)
 - 0°C 至 +125°C 范围内的温度系数：10ppm/°C
- 高精度：
 - 增益误差 (分流和放大器)：0.3% (最大值)
 - 偏移电流：50mA (最大值, INA250A2-Q1)
- 四种增益可供选择：
 - INA250A1-Q1: 200mV/A
 - INA250A2-Q1: 500mV/A
 - INA250A3-Q1: 800mV/A
 - INA250A4-Q1: 2V/A
- 宽共模电压范围：-0.1V 至 36V
- 额定运行温度范围：-40°C 至 +125°C

2 应用

- 车身控制模块
- 直流/直流转换器
- 电池管理系统
- 引擎控制系统
- 悬架系统

3 说明

INA250-Q1 是符合汽车级标准的电压输出、电流感测放大器系列，其集成了一个内部精密分流电阻，能够在 0V 至 36V 共模电压范围上实现高精度电流测量，并且与电源电压无关。

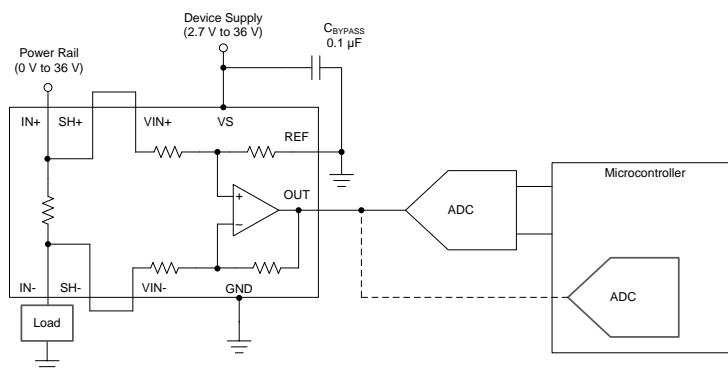
INA250-Q1 系列提供四级输出电压：200mV/A、500mV/A、800mV/A 和 2V/A。该器件已经过完全测试，可在 +125°C 最高温度下提供高达 10A 的持续电流。INA250-Q1 器件由 2.7V 至 36V 的单一电源供电，最大供电电流为 300μA。INA250-Q1 的所有增益版本均在扩展级运行温度范围 (-40°C 至 +125°C) 内额定运行，并且采用薄型小外形尺寸 (TSSOP)-16 封装。

器件信息⁽¹⁾

器件型号	封装	封装尺寸 (标称值)
INA250-Q1	TSSOP (16)	5.00mm x 4.40mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

简化电路原理图



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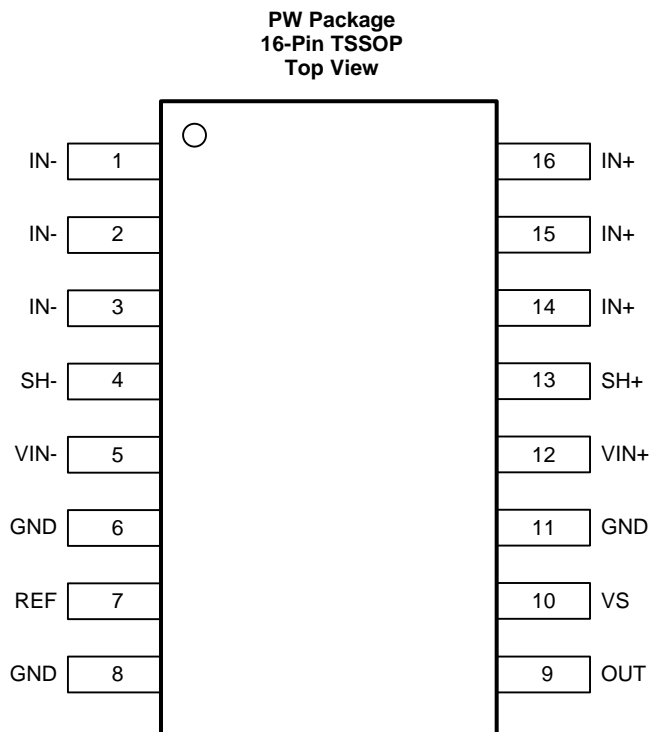
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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Original (July 2016) to Revision A	Page
• 已将文档状态从“产品预览”改为“量产数据”	1
• Changed maximum charged-device model ESD value from ± 750 to ± 1000	4
• Changed maximum I_B values in the <i>Electrical Characteristics</i> table from ± 35 to ± 40	6

5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
GND	6, 8, 11	Analog	Ground
IN-	1, 2, 3	Analog input	Connect to load
IN+	14, 15, 16	Analog input	Connect to supply
OUT	9	Analog output	Output voltage
REF	7	Analog input	Reference voltage, 0 V to VS (up to 18 V)
SH-	4	Analog output	Kelvin connection to internal shunt. Connect to VIN- if no filtering is needed. See Figure 33 for filter recommendations.
SH+	13	Analog output	Kelvin connection to internal shunt. Connect to VIN+ if no filtering is needed. See Figure 33 for filter recommendations.
VIN-	5	Analog input	Voltage input from load side of shunt resistor.
VIN+	12	Analog input	Voltage input from supply side of shunt resistor.
VS	10	Analog	Device power supply, 2.7 V to 36 V

6 Specifications

6.1 Absolute Maximum Ratings

 over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Supply voltage (VS)			40	V
Analog input current	Continuous current		±15	A
Analog inputs (IN+, IN-)	Common-mode	GND – 0.3	40	V
Analog inputs (VIN+, VIN-)	Common-mode	GND – 0.3	40	V
	Differential (VIN+) – (VIN-)	–40	40	
Analog inputs (REF)		GND – 0.3	VS + 0.3	V
Analog outputs (SH+, SH-)	Common-mode	GND – 0.3	40	V
Analog outputs (OUT)		GND – 0.3	(VS + 0.3) up to 18	V
Temperature	Operating, TA	–55	150	°C
	Junction, TJ		150	
	Storage, Tstg	–65	150	

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

6.2 ESD Ratings

		VALUE	UNIT
V(ESD)	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾	±2000
		Charged-device model (CDM), per AEC Q100-011	±1000

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

		MIN	NOM	MAX	UNIT
V _{CM}	Common-mode input voltage	0		36	V
VS	Operating supply voltage	2.7		36	V
TA	Operating free-air temperature	–40		125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		INA250-Q1	
		PW (TSSOP)	
		16 PINS	
			UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	104.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	42.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	48.5	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	4.5	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	48	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see [Semiconductor and IC Package Thermal Metrics](#) (SPRA953).

6.5 Electrical Characteristics

 at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $V_{IN+} = 12\text{ V}$, $V_{REF} = 2.5\text{ V}$, $I_{SENSE} = I_{IN+} = 0\text{ A}$, unless otherwise noted.

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT	
INPUT						
V_{CM}	Common-mode input range	-0.1		36	V	
CMR	Common-mode rejection	INA250A1-Q1, $V_{IN+} = 0\text{ V to }36\text{ V}$, $T_A = -40^\circ\text{C to }125^\circ\text{C}$	94	102	dB	
		INA250A2-Q1, $V_{IN+} = 0\text{ V to }36\text{ V}$, $T_A = -40^\circ\text{C to }125^\circ\text{C}$	97	110		
		INA250A3-Q1, $V_{IN+} = 0\text{ V to }36\text{ V}$, $T_A = -40^\circ\text{C to }125^\circ\text{C}$	106	114		
		INA250A4-Q1, $V_{IN+} = 0\text{ V to }36\text{ V}$, $T_A = -40^\circ\text{C to }125^\circ\text{C}$	108	118		
I_{OS}	Offset current, RTI ⁽¹⁾	INA250A1-Q1, $I_{SENSE} = 0\text{ A}$		± 15	± 100	mA
		INA250A2-Q1, $I_{SENSE} = 0\text{ A}$		± 12.5	± 50	
		INA250A3-Q1, $I_{SENSE} = 0\text{ A}$		± 5	± 30	
		INA250A4-Q1, $I_{SENSE} = 0\text{ A}$		± 5	± 20	
dI_{OS}/dT	RTI versus temperature	$T_A = -40^\circ\text{C to }125^\circ\text{C}$		25	250	$\mu\text{A}/^\circ\text{C}$
PSR		$V_S = 2.7\text{ V to }36\text{ V}$, $T_A = -40^\circ\text{C to }125^\circ\text{C}$		± 0.03	± 1	mA/V
I_B	Input bias current	I_{B+} , I_{B-} , $I_{SENSE} = 0\text{ A}$		± 28	± 40	μA
V_{REF}	Reference input range ⁽²⁾		0	(VS) up to 18	V	
SHUNT RESISTOR⁽³⁾						
R_{SHUNT}	Shunt resistance (SH+ to SH-)	Equivalent resistance when used with onboard amplifier	1.998	2	2.002	m Ω
		Used as stand-alone resistor ⁽⁴⁾	1.9	2	2.1	
	Package resistance	IN+ to IN-		4.5		m Ω
	Resistor temperature coefficient	$T_A = -40^\circ\text{C to }125^\circ\text{C}$		15	ppm/ $^\circ\text{C}$	
		$T_A = -40^\circ\text{C to }0^\circ\text{C}$		50		
		$T_A = 0^\circ\text{C to }125^\circ\text{C}$		10		
I_{SENSE}	Maximum continuous current ⁽⁵⁾	$T_A = -40^\circ\text{C to }85^\circ\text{C}$			± 15	A
	Shunt short time overload	$I_{SENSE} = 30\text{ A for }5\text{ seconds}$		$\pm 0.05\%$		
	Shunt thermal shock	$-65^\circ\text{C to }150^\circ\text{C}$, 500 cycles		$\pm 0.1\%$		
	Shunt resistance to solder heat	260 $^\circ\text{C}$ solder, 10 s		$\pm 0.1\%$		
	Shunt high temperature exposure	1000 hours, $T_A = 150^\circ\text{C}$		$\pm 0.15\%$		
	Shunt cold temperature storage	24 hours, $T_A = -65^\circ\text{C}$		$\pm 0.025\%$		

(1) RTI = referred-to-input.

(2) The supply voltage range maximum is 36 V, but the reference voltage cannot be higher than 18 V.

 (3) See the [Integrated Shunt Resistor](#) section for additional information regarding the integrated current-sensing resistor.

 (4) The internal shunt resistor is intended to be used with the internal amplifier and is not intended to be used as a stand-alone resistor. See the [Integrated Shunt Resistor](#) section for more information.

 (5) See [Figure 30](#) and the [Layout](#) section for additional information on the current derating and layout recommendations to improve the current handling capability of the device at higher temperatures.

Electrical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $V_{IN+} = 12\text{ V}$, $V_{REF} = 2.5\text{ V}$, $I_{SENSE} = I_{N+} = 0\text{ A}$, unless otherwise noted.

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNIT
OUTPUT						
G	Gain	INA250A1-Q1		200		mV/A
		INA250A2-Q1		500		
		INA250A3-Q1		800		
		INA250A4-Q1		2		V/A
	System gain error ⁽⁶⁾	$I_{SENSE} = -10\text{ A to }10\text{ A}$, $T_A = 25^\circ\text{C}$		$\pm 0.05\%$	$\pm 0.3\%$	ppm/ $^\circ\text{C}$
		$I_{SENSE} = -10\text{ A to }10\text{ A}$, $T_A = -40^\circ\text{C to }125^\circ\text{C}$			$\pm 0.75\%$	
		$T_A = -40^\circ\text{C to }125^\circ\text{C}$			45	
	Nonlinearity error	$I_{SENSE} = 0.5\text{ A to }10\text{ A}$		$\pm 0.03\%$		
R_O	Output impedance			1.5		Ω
	Maximum capacitive load	No sustained oscillation		1		nF
VOLTAGE OUTPUT⁽⁷⁾						
	Swing to V_S power-supply rail	$R_L = 10\text{ k}\Omega$ to GND		$(V_S) - 0.1$	$(V_S) - 0.2$	V
	Swing to GND	$R_L = 10\text{ k}\Omega$ to GND		$(V_{GND}) + 25$	$(V_{GND}) + 50$	mV
FREQUENCY RESPONSE						
BW	Bandwidth	INA250A1-Q1, $C_L = 10\text{ pF}$		50		kHz
		INA250A2-Q1, $C_L = 10\text{ pF}$		50		
		INA250A3-Q1, $C_L = 10\text{ pF}$		35		
		INA250A4-Q1, $C_L = 10\text{ pF}$		11		
SR	Slew rate	$C_L = 10\text{ pF}$		0.2		V/ μs
NOISE, RTI⁽¹⁾						
	Voltage noise density	INA250A1-Q1		51		nV/ $\sqrt{\text{Hz}}$
		INA250A2-Q1		35		
		INA250A3-Q1		37		
		INA250A4-Q1		27		
POWER SUPPLY						
V_S	Operating voltage range		2.7		36	V
I_Q	Quiescent current	$T_A = -40^\circ\text{C to }125^\circ\text{C}$		200	300	μA
TEMPERATURE RANGE						
	Specified range		-40		125	$^\circ\text{C}$

(6) System gain error includes amplifier gain error and the integrated sense resistor tolerance. System gain error does not include the stress related characteristics of the integrated sense resistor. These characteristics are described in the [Shunt Resistor](#) section of the [Electrical Characteristics](#) table.

(7) See [Output Voltage Swing vs Output Current](#) (图 19).

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6.6 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $V_{IN+} = 12\text{ V}$, $V_{REF} = 2.5\text{ V}$, $I_{SENSE} = I_{IN+} = 0\text{ A}$, unless otherwise noted.

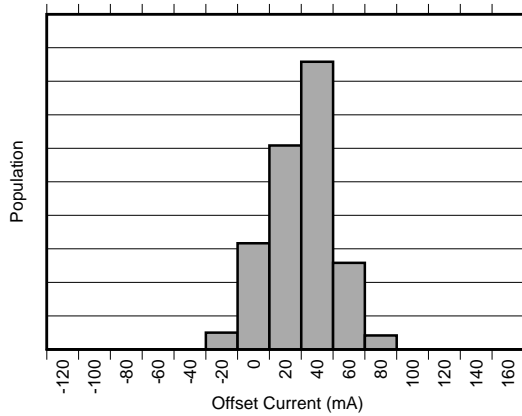


图 1. INA250A1-Q1 Input Offset Distribution

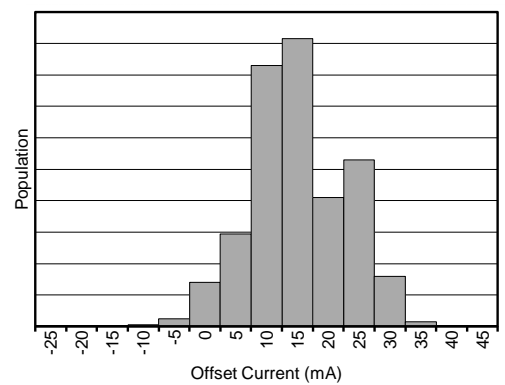


图 2. INA250A2-Q1 Input Offset Distribution

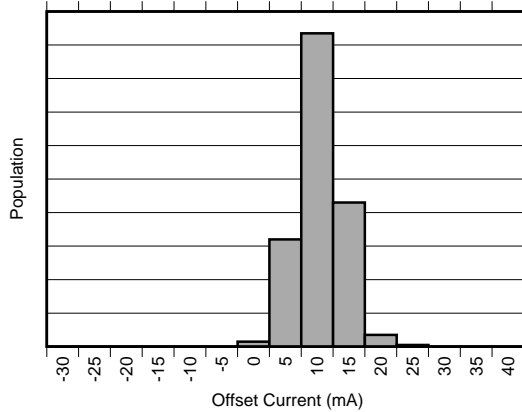


图 3. INA250A3-Q1 Input Offset Distribution

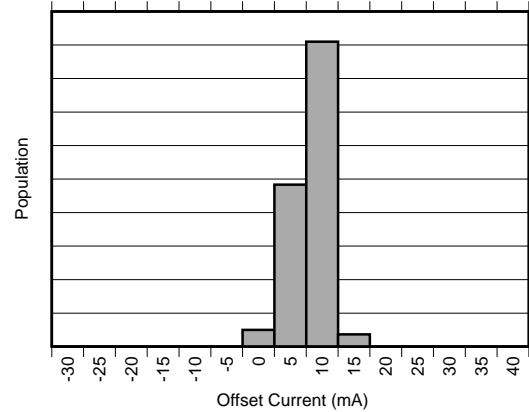


图 4. INA250A4-Q1 Input Offset Distribution

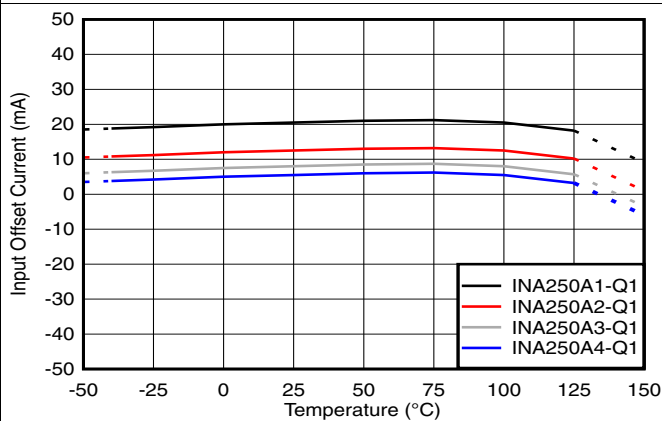


图 5. Input Offset vs Temperature

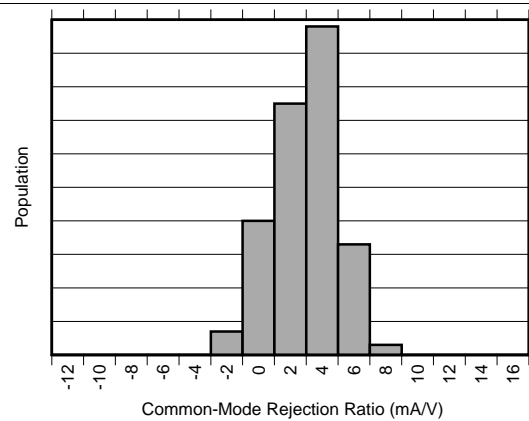


图 6. INA250A1-Q1 Common-Mode Rejection Ratio Distribution

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $V_{IN+} = 12\text{ V}$, $V_{REF} = 2.5\text{ V}$, $I_{SENSE} = I_{IN+} = 0\text{ A}$, unless otherwise noted.

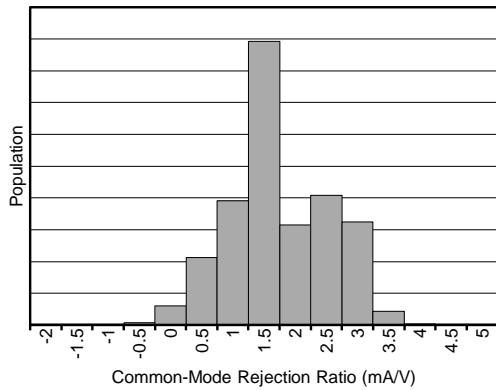


图 7. INA250A2-Q1 Common-Mode Rejection Ratio Distribution

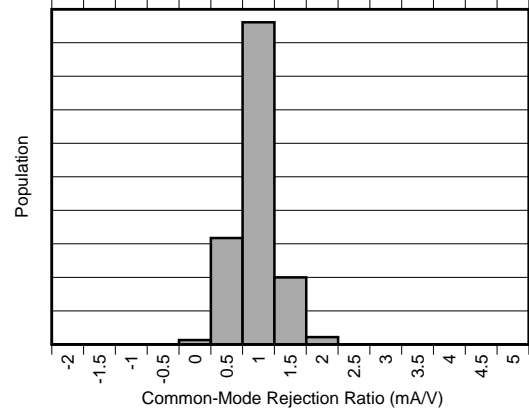


图 8. INA250A3-Q1 Common-Mode Rejection Ratio Distribution

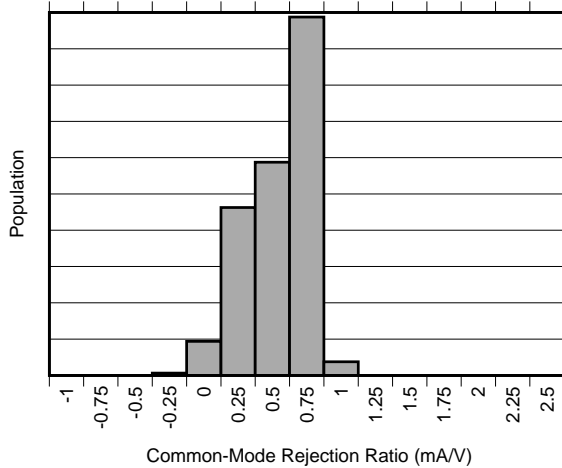


图 9. INA250A4-Q1 Common-Mode Rejection Ratio Distribution

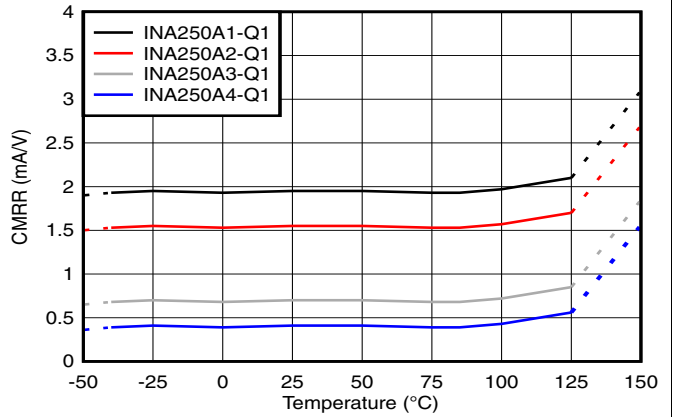


图 10. Common-Mode Rejection Ratio vs Temperature

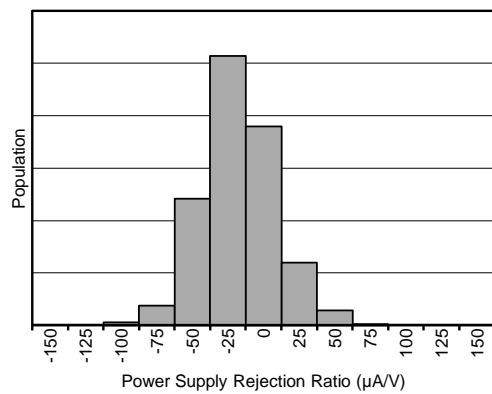


图 11. Power-Supply Rejection Ratio Distribution

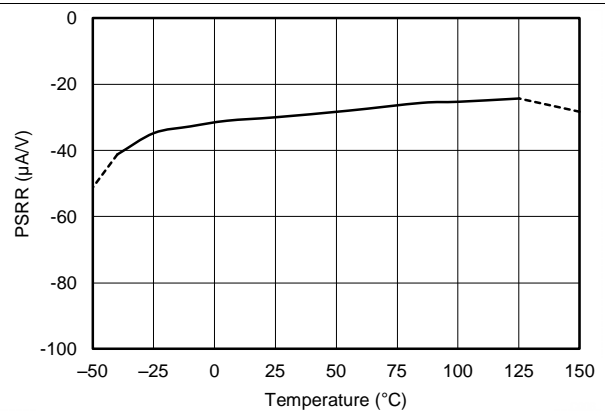


图 12. Power-Supply Rejection Ratio vs Temperature

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $V_{IN+} = 12\text{ V}$, $V_{REF} = 2.5\text{ V}$, $I_{SENSE} = I_{IN+} = 0\text{ A}$, unless otherwise noted.

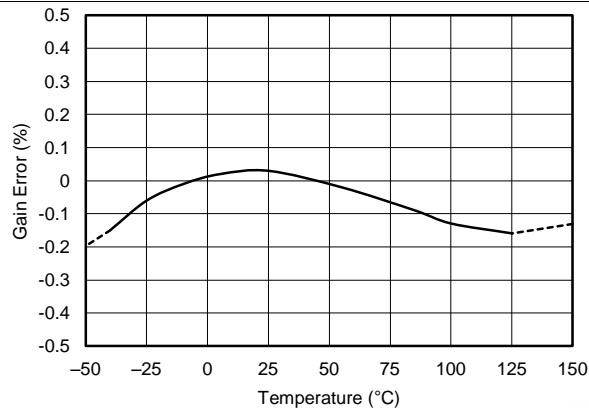
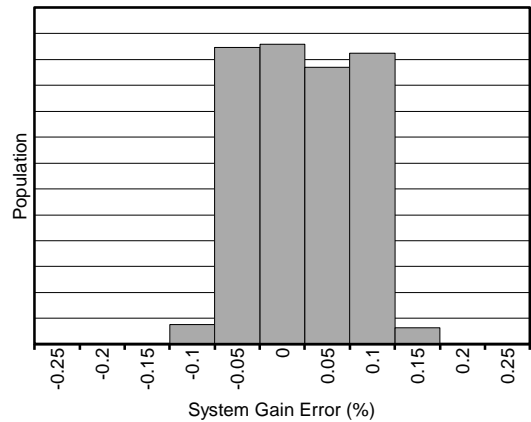


图 13. System Gain Error vs Temperature



System gain error = R_{SHUNT} error + amplifier gain error, load current = 10 A

图 14. System Gain Error Distribution

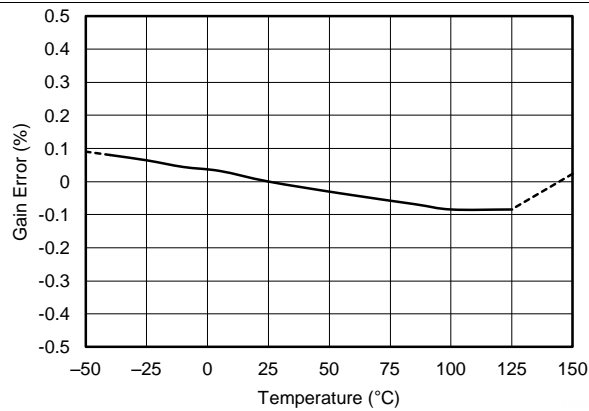
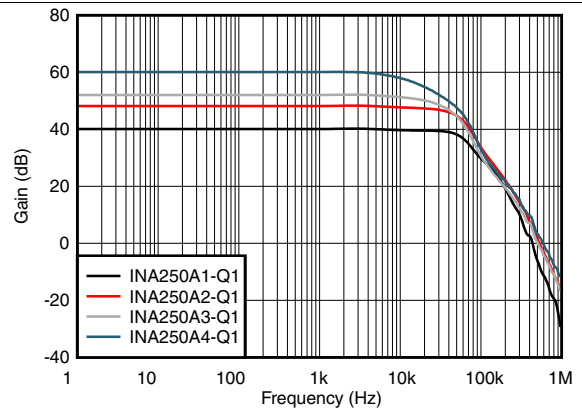
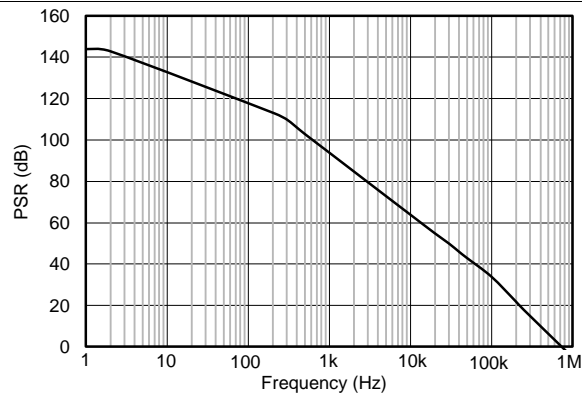


图 15. Amplifier Gain Error vs Temperature



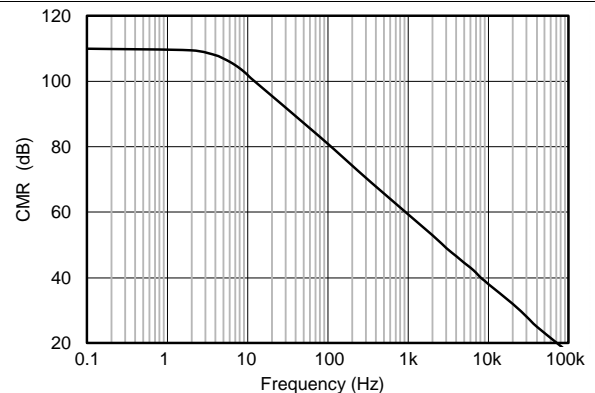
$V_{CM} = 12\text{ V}$, $I_{SENSE} = 500\text{ mA}_{APP}$

图 16. Amplifier Gain vs Frequency



$V_{CM} = 12\text{ V}$, $V_{REF} = 2.5\text{ V}$, $I_{SENSE} = 0\text{ A}$,
 $V_S = 5\text{ V} + 250\text{-mV sine disturbance}$

图 17. Power-Supply Rejection vs Frequency

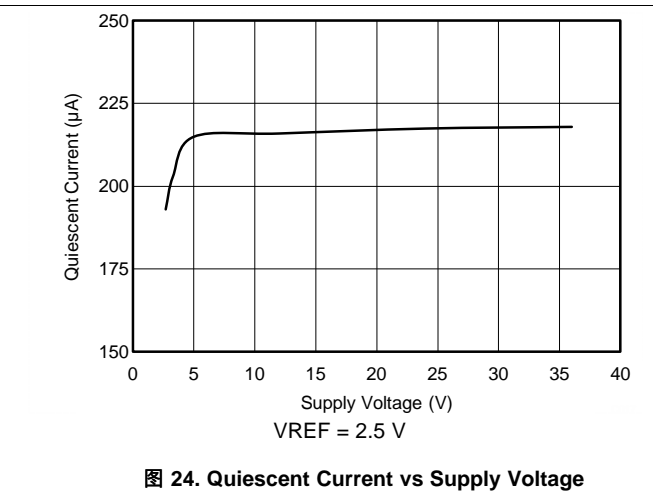
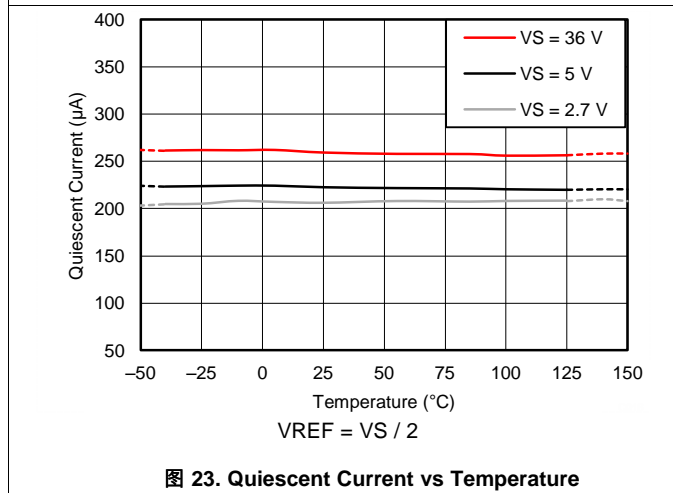
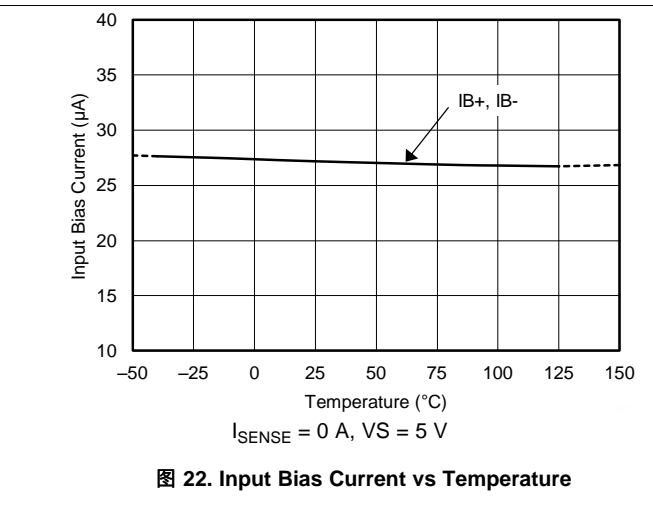
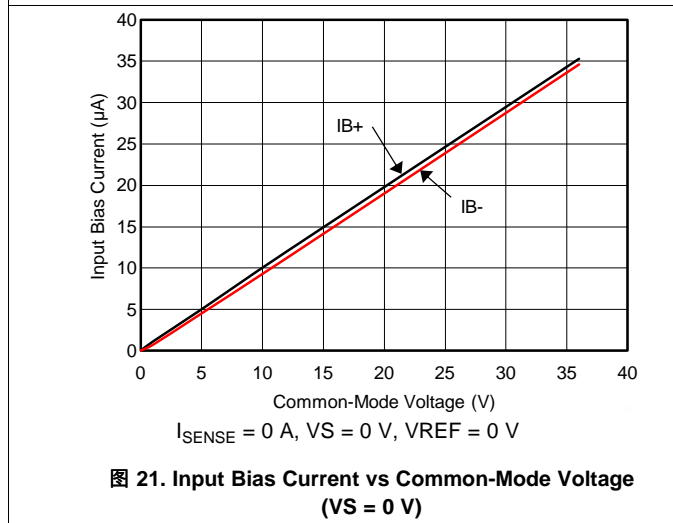
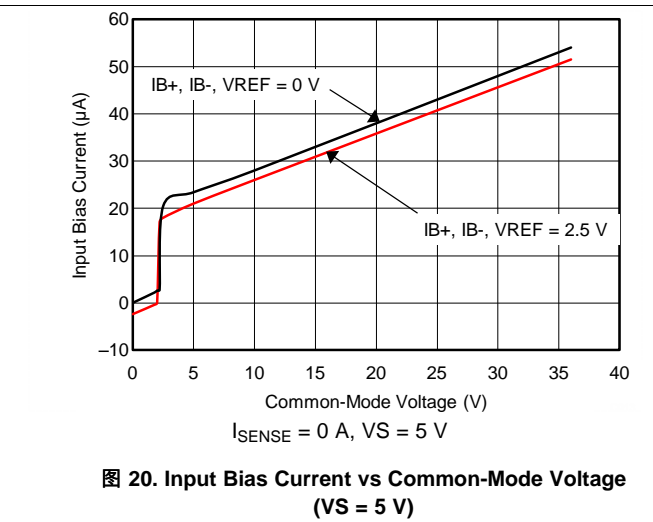
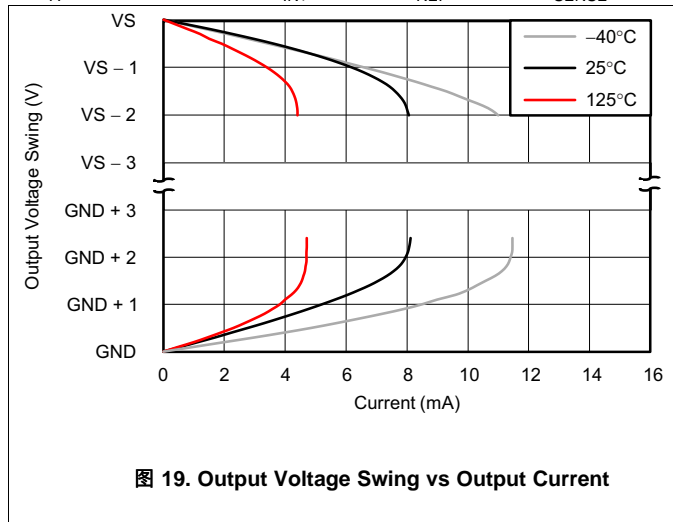


$V_S = 5\text{ V}$, $V_{REF} = 2.5\text{ V}$, $I_{SENSE} = 0\text{ A}$, $V_{CM} = 1\text{-V sine wave}$

图 18. Common-Mode Rejection vs Frequency

Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $V_{IN+} = 12\text{ V}$, $V_{REF} = 2.5\text{ V}$, $I_{SENSE} = I_{IN+} = 0\text{ A}$, unless otherwise noted.



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Typical Characteristics (接下页)

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $V_{IN+} = 12\text{ V}$, $V_{REF} = 2.5\text{ V}$, $I_{SENSE} = I_{IN+} = 0\text{ A}$, unless otherwise noted.

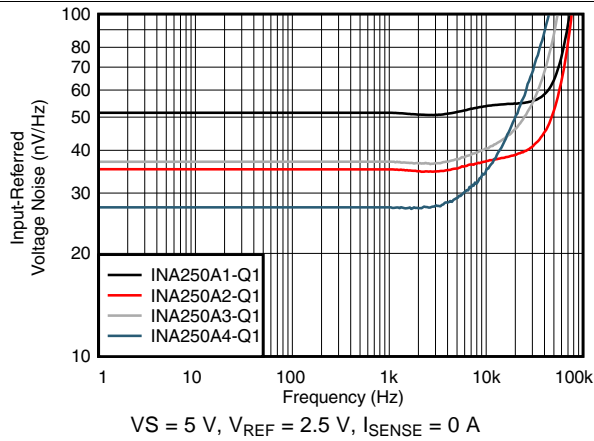


图 25. Input-Referred Voltage Noise vs Frequency

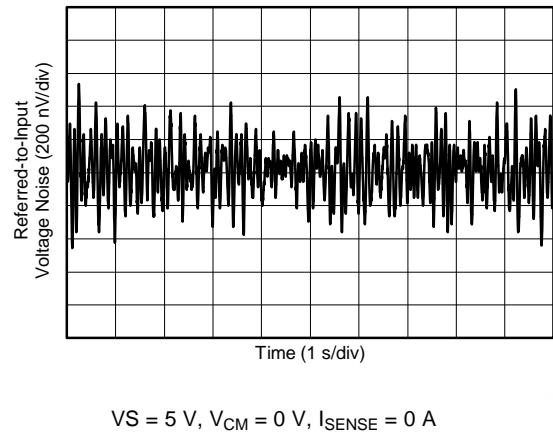


图 26. 0.1-Hz to 10-Hz Voltage Noise (Referred-to-Input)

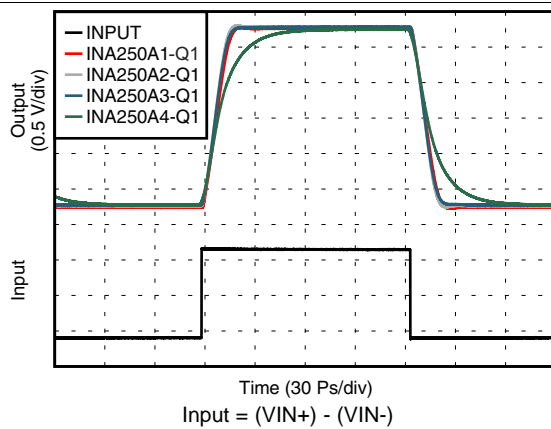


图 27. Step Response

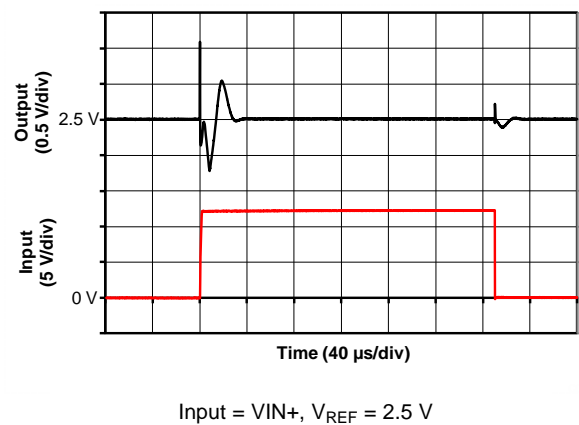


图 28. Common-Mode Transient Response

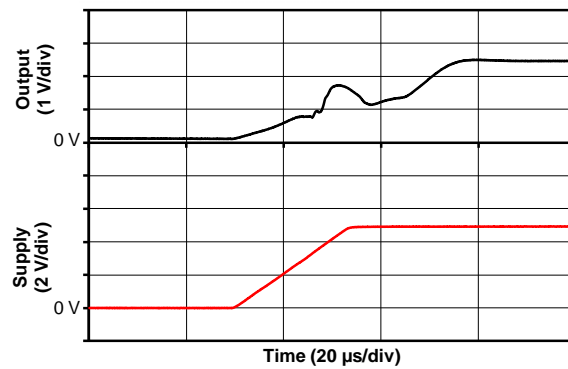


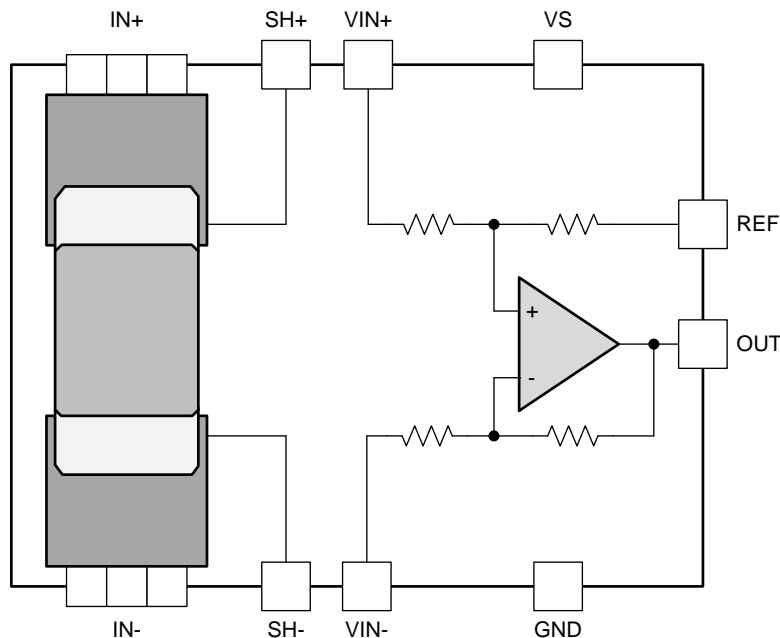
图 29. Start-Up Response

7 Detailed Description

7.1 Overview

The INA250-Q1 features a 2-m Ω , precision, current-sensing resistor and a 36-V common-mode, zero-drift topology, precision, current-sensing amplifier integrated into a single package. High precision measurements are enabled through the matching of the shunt resistor value and the current-sensing amplifier gain providing a highly-accurate, system-calibrated solution. Multiple gain versions are available to allow for the optimization of the desired full-scale output voltage based on the target current range expected in the application.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Integrated Shunt Resistor

The INA250-Q1 features a precise, low-drift, current-sensing resistor to allow for precision measurements over the entire specified temperature range of -40°C to $+125^{\circ}\text{C}$. The integrated current-sensing resistor ensures measurement stability overtemperature and improves layout and board constraint difficulties common in high precision measurements.

The onboard current-sensing resistor is designed as a 4-wire (or Kelvin) connected resistor that enables accurate measurements through a force-sense connection. Connecting the amplifier inputs pins (VIN $-$ and VIN $+$) to the sense pins of the shunt resistor (SH $-$ and SH $+$) eliminates many of the parasitic impedances commonly found in typical very-low sensing-resistor level measurements. Although the sense connection of the current-sensing resistor may be accessed through the SH $+$ and SH $-$ pins, this resistor is not intended to be used as a stand-alone component. The INA250-Q1 device is system-calibrated to ensure that the current-sensing resistor and current-sensing amplifier are both precisely matched to one another. Using the shunt resistor without the onboard amplifier results in a current-sensing resistor tolerance of approximately 5%. To achieve the optimized system gain specification, the onboard sensing resistor must be used with the internal current-sensing amplifier.

Feature Description (接下页)

The INA250-Q1 has approximately 4.5-m Ω of package resistance. 2 m Ω of this total package resistance is a precisely-controlled resistance from the Kelvin-connected current-sensing resistor used by the amplifier. The power dissipation requirements of the system and package are based on the total 4.5-m Ω package resistance between the IN+ and IN– pins. The heat dissipated across the package when current flows through the device ultimately determines the maximum current that may be safely handled by the package. The current consumption of the silicon is relatively low, leaving the total package resistance carrying the high load current as the primary contributor to the total power dissipation of the package. The maximum safe-operating current level ensures that the heat dissipated across the package is limited so that the resistor and the package are not damaged, and the internal junction temperature of the silicon does not exceed a +150°C limit.

External factors (such as ambient temperature, external air flow, and PCB layout) may contribute to how effectively the heat developed from the current flowing through the total package resistance may be removed from the device. Under the conditions of no air flow, a maximum ambient temperature of +85°C, and 1-oz. copper input power planes, the INA250-Q1 device can accommodate continuous current levels up to 15 A. As shown in 图 30, the current handling capability is derated at temperatures above the +85°C level with safe operation up to 10 A at a +125°C ambient temperature. With air flow and larger 2-oz. copper input power planes, the INA250-Q1 may safely accommodate continuous current levels up to 15 A over the entire –40°C to +125°C temperature range.

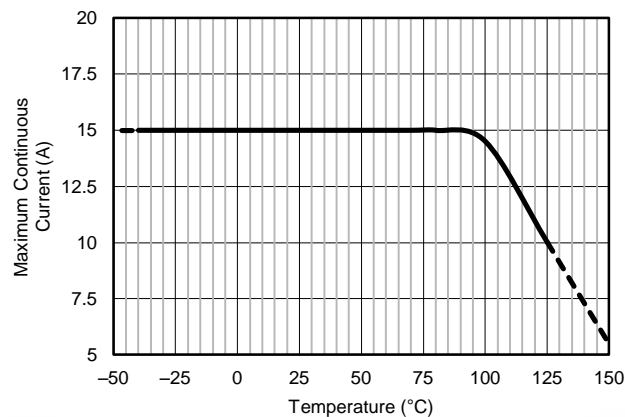


图 30. Maximum Current vs Temperature

7.3.2 Short-Circuit Duration

The INA250-Q1 features a physical shunt resistance that can withstand current levels higher than the continuous handling limit of 15 A without sustaining damage to the current-sensing resistor or the current-sensing amplifier if the excursions are brief. 图 31 shows the short-circuit duration curve for the INA250-Q1.

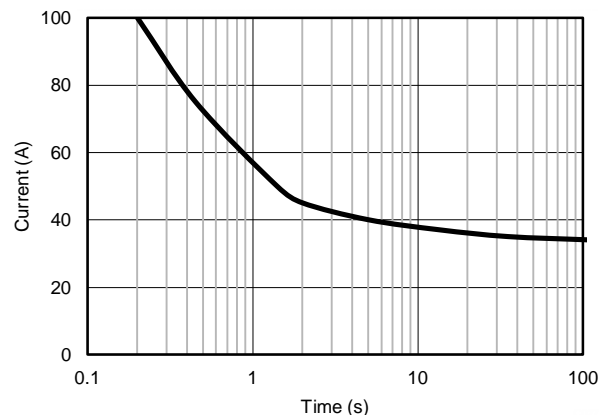


图 31. Short-Circuit Duration

Feature Description (接下页)

7.3.3 Temperature Stability

System calibration is common for many industrial applications to eliminate initial component and system-level errors that may be present. A system-level calibration may reduce the initial accuracy requirement for many of the individual components because the calibration procedure eliminates these errors associated with the components. Performing this calibration may enable precision measurements at the system calibration temperature, but as the system temperature changes as a result of external ambient changes or self heating, measurement errors are reintroduced. Without using accurate temperature compensation in addition to the initial adjustment, the calibration procedure is ineffective in accounting for these temperature-induced changes. One of the primary benefits of the very-low-temperature coefficient of the INA250-Q1 (including the integrated current-sensing resistor and current-sensing amplifier) is that the device measurement remains highly accurate, even when the temperature changes throughout the specified temperature range.

The drift performance of the integrated current-sensing resistor is shown in [图 32](#). Although several temperature ranges are specified in the [Electrical Characteristics](#) table, applications operating in ranges other than those described may use [图 32](#) to determine how much variance in the shunt resistor value may be expected. As with any resistive element, the tolerance of the component varies when exposed to different temperature conditions. For the current-sensing resistor integrated in the INA250-Q1, the resistor varies more when operating in temperatures ranging from -40°C to 0°C than when operating in ranges from 0°C to $+125^{\circ}\text{C}$. However, even in the -40°C to 0°C temperature range, the drift is still low at 25 ppm/ $^{\circ}\text{C}$.

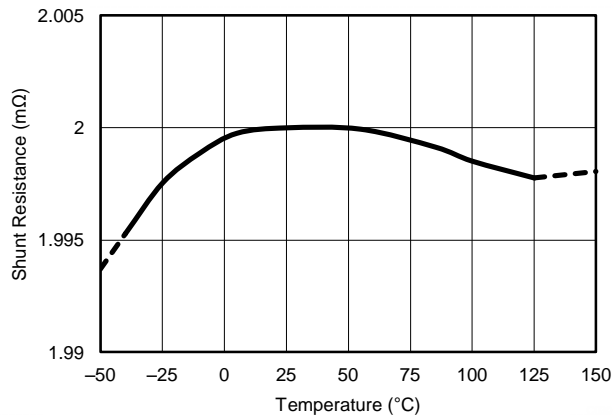


图 32. Sensing Resistor vs Temperature

An additional aspect to consider is that when current flows through the current-sensing resistor, power dissipates across this component. This dissipated power results in an increase in the internal temperature of the package, including the integrated sensing resistor. This resistor self-heating effect results in an increase of the resistor temperature helping to move the component out of the colder, wider drift temperature region.

Device Functional Modes (接下页)

However, the addition of external series resistance at the input pins to the amplifier creates an additional error in the measurement. If possible, keep the value of these series resistors to 10 Ω or less to reduce the affect to accuracy. The internal bias network illustrated in 图 33 at the input pins creates a mismatch in input bias currents when a differential voltage is applied between the input pins, as shown in 图 34.

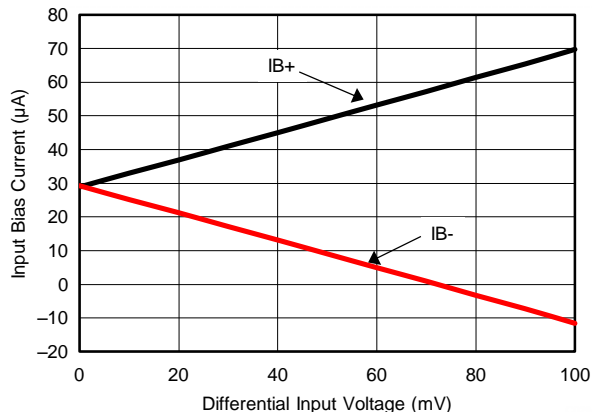


图 34. Input Bias Current vs Differential Input Voltage

7.4.2.1 Calculating Gain Error Resulting from External Filter Resistance

If additional external series filter resistors are added to the circuit, the mismatch in bias currents results in a mismatch of voltage drops across the filter resistors. This mismatch creates a differential error voltage that subtracts from the voltage developed across the Kelvin connection of the shunt resistor, thus reducing the voltage that reaches the amplifier input terminals. Without the additional series resistance, the mismatch in input bias currents has little effect on device operation as a result of the low input bias current of the amplifier and the typically low impedance of the traces between the shunt and amplifier input pins. The amount of error these external filter resistors add to the measurement may be calculated using 公式 3, where the gain error factor is calculated using 公式 2.

The amount of variance between the differential voltage present at the device input relative to the voltage developed at the shunt resistor is based both on the external series resistance value as well as the internal input resistors, R_{INT} , as shown in 图 33. The reduction of the shunt voltage reaching the device input pins appears as a gain error when comparing the output voltage relative to the voltage across the shunt resistor. A factor may be calculated to determine the amount of gain error that is introduced by the addition of external series resistance. 公式 2 calculates the expected deviation from the shunt voltage compared to the expected voltage at the device input pins.

$$\text{Gain Error Factor} = \frac{(1250 \times R_{INT})}{(1250 \times R_S) + (1250 \times R_{INT}) + (R_S \times R_{INT})}$$

where:

- R_{INT} is the internal input resistor and
- R_S is the external series resistance

$$\text{Gain Error (\%)} = 100 - (100 \times \text{Gain Error Factor}) \quad (3)$$

With the adjustment factor equation including the device internal input resistance, this factor varies with each gain version, as shown in 表 1. 表 2 lists the gain error factor for each individual device.

公式 3 calculates the expected gain error from the addition of the external series resistors.

表 1. Input Resistance

DEVICE	GAIN	R_{INT}
INA250A1-Q1	200 mV/A	50 kΩ

Device Functional Modes (接下页)

表 1. Input Resistance (接下页)

DEVICE	GAIN	R _{INT}
INA250A2-Q1	500 mV/A	20 kΩ
INA250A3-Q1	800 mV/A	12.5 kΩ
INA250A4-Q1	2 V/A	5 kΩ

表 2. Device Gain Error Factor

DEVICE	SIMPLIFIED GAIN ERROR FACTOR
INA250A1-Q1	$\frac{50,000}{(41 \cdot R_S) + 50,000}$
INA250A2-Q1	$\frac{20,000}{(17 \cdot R_S) + 20,000}$
INA250A3-Q1	$\frac{12,500}{(11 \cdot R_S) + 12,500}$
INA250A4-Q1	$\frac{1,000}{R_S + 1,000}$

For example, using an INA250A2-Q1 device and the corresponding gain error equation from 表 2, a series resistance of 10-Ω results in a gain error factor of 0.991. The corresponding gain error is then calculated using 公式 3, resulting in a gain error of approximately 0.84% because of the external 10-Ω series resistors.

7.4.3 Shutting Down the Device

Although the device does not have a shutdown pin, the low power consumption allows for the device to be powered from the output of a logic gate or transistor switch that may turn on and turn off the voltage connected to the device power-supply pin. However, in current-shunt monitoring applications, there is also a concern for how much current is drained from the shunt circuit in shutdown conditions. Evaluating this current drain involves considering the simplified schematic in shutdown mode, as shown in 图 35.

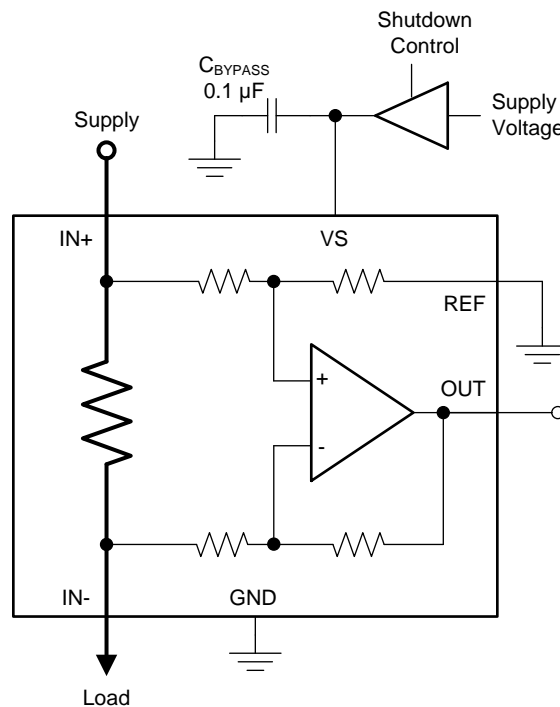


图 35. Shutting Down the Device

Note that there is typically an approximate 1-M Ω impedance (from the combination of the feedback and input resistors) from each device input to the REF pin. The amount of current flowing through these pins depends on the respective configuration. For example, if the REF pin is grounded, calculating the effect of the 1-M Ω impedance from the shunt to ground is straightforward. However, if the reference or op amp is powered when the device is shut down, the calculation is direct. Instead of assuming 1 M Ω to ground, assume 1 M Ω to the reference voltage. If the reference or op amp is also shut down, some knowledge of the reference or op amp output impedance under shutdown conditions is required. For instance, if the reference source functions similar to an open circuit when un-powered, little or no current flows through the 1-M Ω path.

7.4.4 Using the Device with Common-Mode Transients Above 36 V

With a small amount of additional circuitry, the device may be used in circuits subject to transients higher than 36 V (such as in automotive applications). Use only zener diodes or zener-type transient absorbers (sometimes referred to as *transzorb*s); any other type of transient absorber has an unacceptable time delay. Start by adding a pair of resistors, as shown in [Figure 36](#), as a working impedance for the zener. Keeping these resistors as small as possible is preferable; a resistor value of 10- Ω is the most common. This value limits the effect on accuracy with the addition of these external components, as described in the [Input Filtering](#) section. Device interconnections between the shunt resistor and amplifier have a current handling limit of 1 A. Using a 10- Ω resistor limits the allowable transient range to 10 V above the zener clamp so the device is not damaged. Larger resistor values may be used in this protection circuit to accommodate a larger transient voltage range, which results in a larger effect on gain error. Because this circuit limits only short-term transients, many applications are satisfied with a 10- Ω resistor, along with conventional zener diodes of the lowest power rating available.

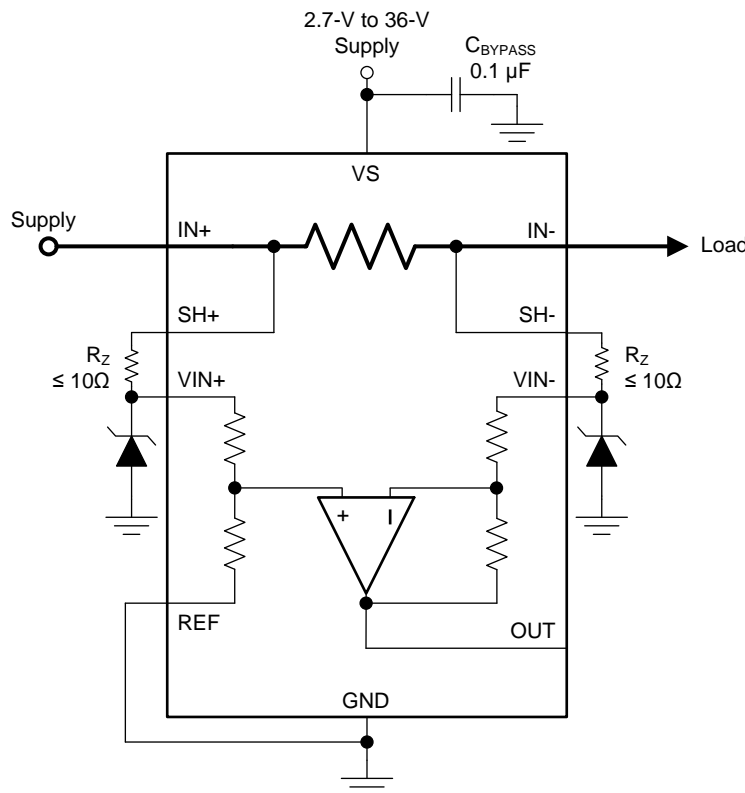


图 36. Device Transient Protection

Typical Applications (接下页)

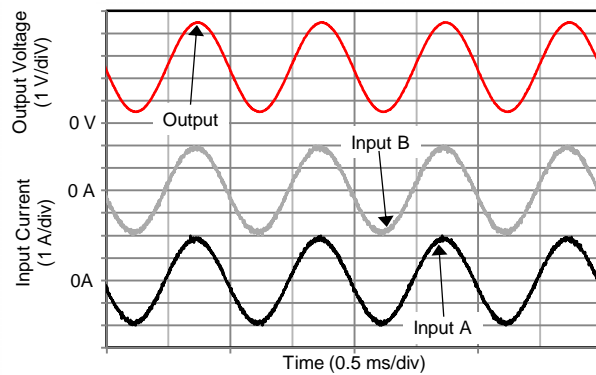
8.2.1.1 Design Requirements

Three daisy-chained devices are illustrated in 图 37. The reference input of the first INA250-Q1 device sets the quiescent level on the output of all the INA250-Q1 devices in the string.

8.2.1.2 Detailed Design Procedure

The outputs of multiple INA250-Q1 devices are easily summed by connecting the output signal of one INA250-Q1 device to the reference input of a second INA250-Q1 device. Summing beyond two devices is possible by repeating this configuration, connecting the output signal of the next INA250-Q1 device to the reference pin of a subsequent INA250-Q1 in the chain. The output signal of the final INA250-Q1 device in this chain includes the current level information for all channels in the chain.

8.2.1.3 Application Curve



$$V_S = 5 \text{ V}, V_{REF} = 2.5 \text{ V}$$

图 38. Daisy-Chain Configuration Output Response

Typical Applications (接下页)

8.2.2 Parallel Multiple INA250-Q1 Devices for Higher Current

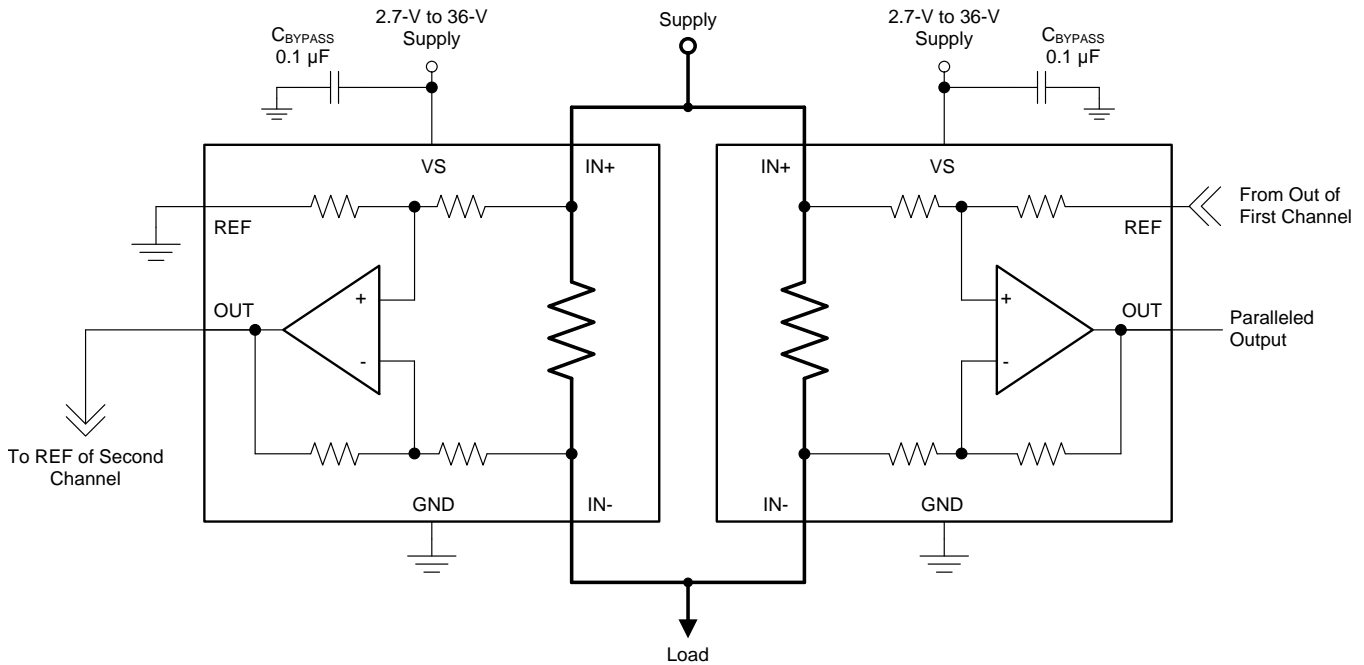


图 39. Parallel Summing Configuration

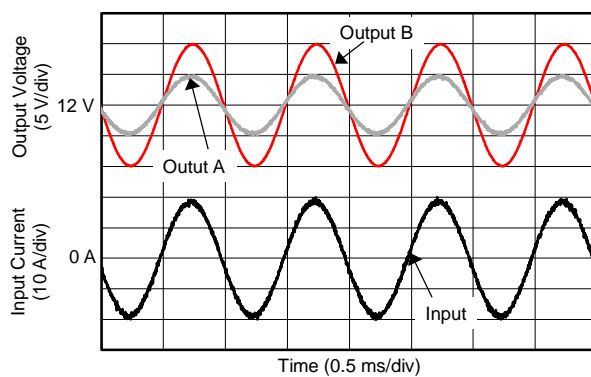
8.2.2.1 Design Requirements

The parallel connection for multiple INA250-Q1 devices may reduce the equivalent overall sense resistance, enabling monitoring of higher current levels than a single device is able to accommodate alone. This configuration also uses a summing arrangement, as described in the [Current Summing](#) section. A parallel summing configuration is shown in [图 39](#).

8.2.2.2 Detailed Design Procedure

With a summing configuration, the output of the first channel is fed into the reference input of the second, adding the distributed measurements back together into a single measured value.

8.2.2.3 Application Curve



$$V_S = 24 \text{ V}, V_{REF} = 12 \text{ V}$$

图 40. Parallel Configuration Output Response

Typical Applications (接下页)

8.2.3 Current Differencing

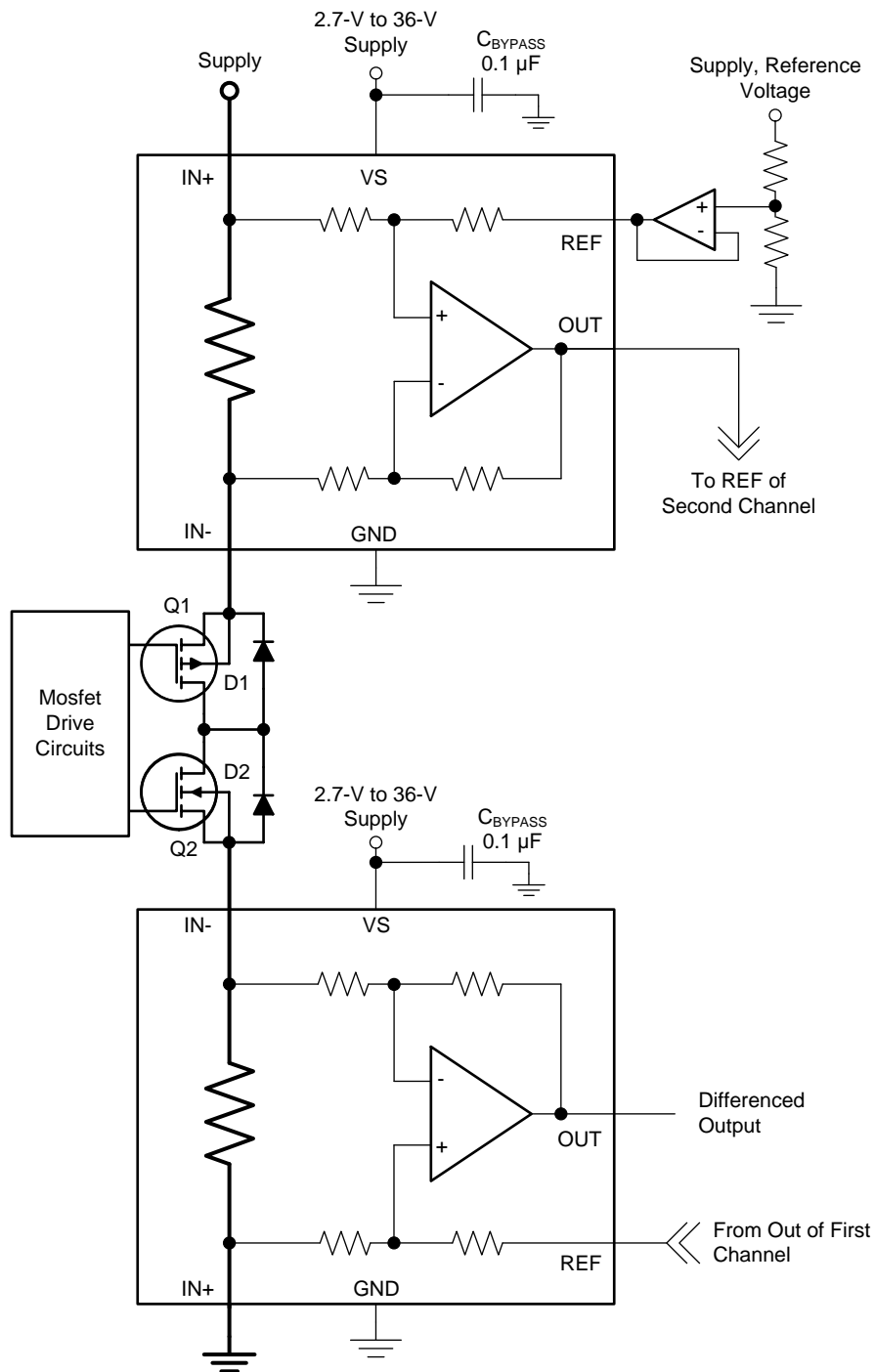


图 41. Current Differencing Configuration

Typical Applications (接下页)

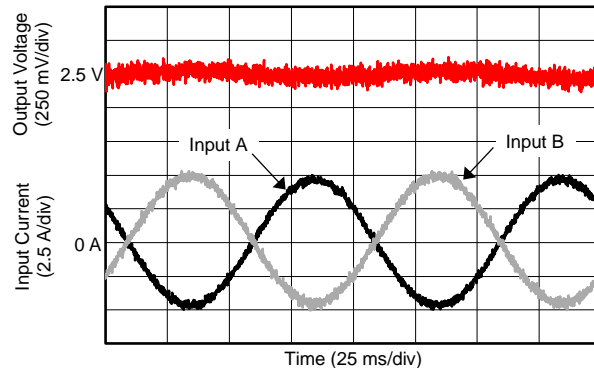
8.2.3.1 Design Requirements

Occasionally, the need may arise to confirm that the current into a load is identical to the current coming out of a load, such as when performing diagnostic testing or fault detection. This procedure requires precision current differencing. This method is the same as current summing, except that the two amplifiers have the respective inputs connected opposite of each other. Under normal operating conditions, the final output is close to the reference value and proportional to any current difference. 图 41 是一个例子，展示了两个 INA250-Q1 设备连接用于电流差分。

8.2.3.2 Detailed Design Procedure

负载电流也可以在第一个通道的输出处直接测量。虽然从技术上讲，这种配置是电流差分，但这种连接（参见图 41）旨在允许上部（正）感测通道报告整体输出中的任何正向 excursion，而下部（负）感测通道报告任何负向 excursion。

8.2.3.3 Application Curve



$$V_S = 5 \text{ V}, V_{REF} = 2.5 \text{ V}$$

图 42. 电流差分配置输出响应

9 Power Supply Recommendations

The input circuitry of the device may accurately measure signals on common-mode voltages beyond the power-supply voltage, V_S . For example, the voltage applied to the V_S power-supply pin may be 5 V, whereas the load power-supply voltage being monitored (the common-mode voltage) may be as high as 36 V. Note that the device may withstand the full 0-V to 36-V range at the input pins, regardless of whether the device has power applied or not. Power-supply bypass capacitors are required for stability, and must be placed as closely as possible to the supply and ground pins of the device. A typical value for this supply bypass capacitor is 0.1 μF . Applications with noisy or high-impedance power supplies may require additional decoupling capacitors to reject power-supply noise.

10 Layout

10.1 Layout Guidelines

- The INA250-Q1 is specified for current handling of up to 10 A over the entire -40°C to $+125^{\circ}\text{C}$ temperature range using a 1-oz. copper pour for the input power plane as well as no external airflow passing over the device.
- The primary current-handling limitation for the INA250-Q1 is how much heat is dissipated inside the package. Efforts to improve heat transfer out of the package and into the surrounding environment improve the ability of the device to handle currents of up to 15 A over the entire -40°C to $+125^{\circ}\text{C}$ temperature range.
- Heat transfer improvements primarily involve larger copper power traces and planes with increased copper thickness (2 oz.) as well as providing airflow to pass over the device. The [INA250EVM](#) (SBOU153) is capable of supporting 15 A at temperatures up to $+125^{\circ}\text{C}$.
- Place the power-supply bypass capacitor as close as possible to the supply and ground pins. TI recommends a bypass capacitor value of $0.1\ \mu\text{F}$. Additional decoupling capacitance may be added to compensate for noisy or high-impedance power supplies.

10.2 Layout Examples

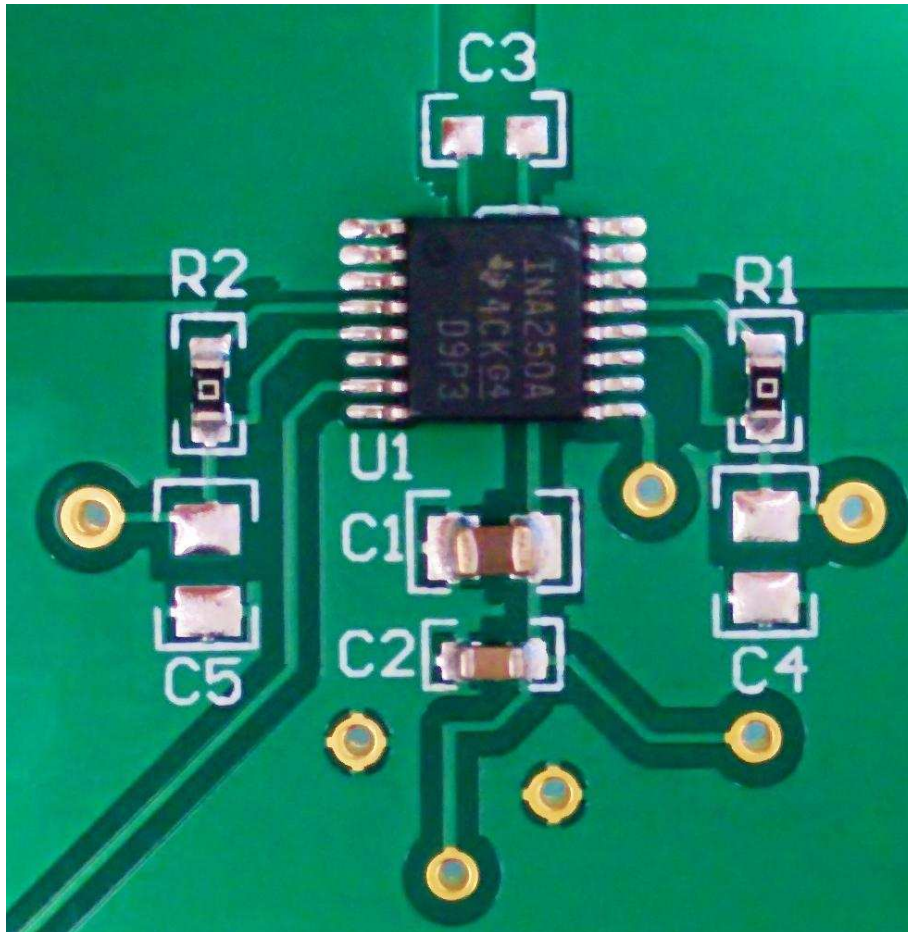


图 43. Recommended Layout

Layout Examples (接下页)

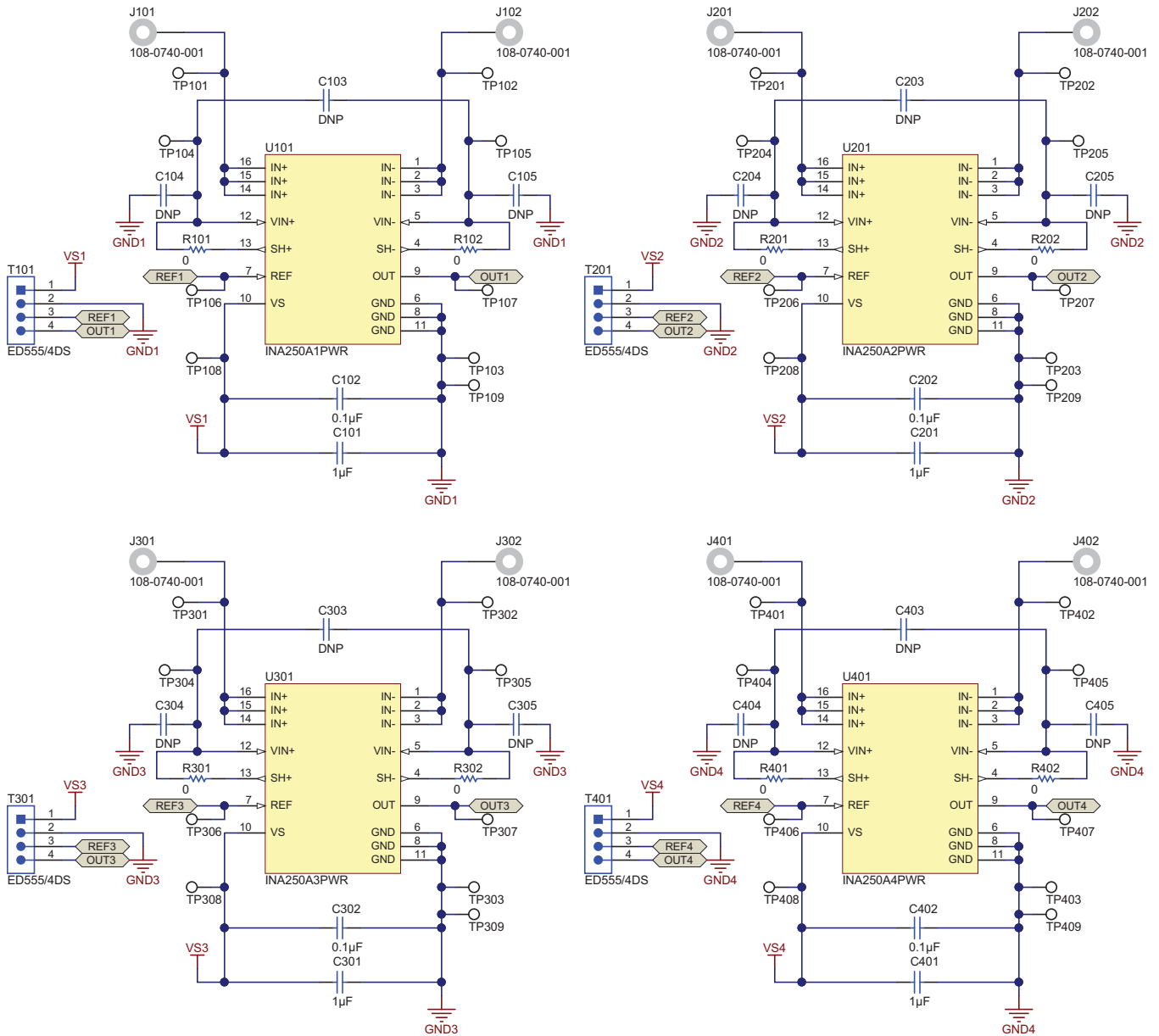


图 44. Recommended Layout Schematic

11 器件和文档支持

11.1 接收文档更新通知

要接收文档更新通知，请访问 www.ti.com.cn 您器件对应的产品文件夹。点击右上角的提醒我 (*Alert me*) 注册后，即可每周定期收到已更改的产品信息。有关更改的详细信息，请查阅已修订文档的修订历史记录。

11.2 文档支持

11.2.1 相关文档

- 《[INA250EVM 用户指南](#)》（文献编号：SBOU153）

11.3 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

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11.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

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数据转换器	www.ti.com.cn/dataconverters	消费电子	www.ti.com.cn/consumer-apps
DLP® 产品	www.dlp.com	能源	www.ti.com.cn/energy
DSP - 数字信号处理器	www.ti.com.cn/dsp	工业应用	www.ti.com.cn/industrial
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邮寄地址: 上海市浦东新区世纪大道1568号, 中建大厦32楼邮政编码: 200122
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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
INA250A1QPWRQ1	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	Q250A1	Samples
INA250A2QPWRQ1	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	Q250A2	Samples
INA250A3QPWRQ1	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	Q250A3	Samples
INA250A4QPWRQ1	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	Q250A4	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) **MSL, Peak Temp.** - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) **Lead finish/Ball material** - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

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NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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